

Power Matters."

Electrical Characteristics (Per IGBT)

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit	
I _{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} =$			100	μA	
V _{CE(sat)}	Collector Emitter Saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		1.5	1.9	V
		$I_C = 50A$	$T_j = 150^{\circ}C$		1.7		v
V _{GE(th)}	Gate Threshold Voltage	$V_{GE} = V_{CE} , \ I_C = 600 \mu A$		5.0	5.8	6.5	V
I _{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				600	nA

Dynamic Characteristics (Per IGBT)

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit	
Cies	Input Capacitance	$\begin{array}{l} V_{GE}=0V\\ V_{CE}=25V \end{array}$			3150		
Coes	Output Capacitance				200		pF
Cres	Reverse Transfer Capacitance	f = 1 MHz		95			
T _{d(on)}	Turn-on Delay Time	Inductive Switch		110			
Tr	Rise Time	$V_{GE} = \pm 15V$		45			
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 300V$ $I_{C} = 50A$		200		ns	
T_{f}	Fall Time	$R_G = 8.2\Omega$		40			
T _{d(on)}	Turn-on Delay Time	Inductive Switch		120			
Tr	Rise Time	$V_{GE} = \pm 15V$		50		ns	
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 300V$ $I_C = 50A$		250			
T _f	Fall Time	$R_G = 8.2\Omega$			60		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 300V$	$T_j = 150^{\circ}C$		0.43		mJ
E _{off}	Turn-off Switching Energy	$I_{\rm C} = 50 {\rm A}$ $R_{\rm G} = 8.2 {\rm \Omega}$	$T_j = 150^{\circ}\mathrm{C}$		1.75		mJ
R _{thJC}	Junction to Case Thermal Resistance					0.85	°C/W

Chopper diode ratings and characteristics (Per diode)

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Peak Repetitive Reverse Voltage					600	V
I _{RM}	Reverse Leakage Current	V _R =600V				250	μΑ
$I_{\rm F}$	DC Forward Current		$Tc = 25^{\circ}C$		50		А
\mathbf{V}_{F}	Diode Forward Voltage	$\begin{split} I_F &= 50A \\ V_{GE} &= 0V \end{split}$	$T_j = 25^{\circ}C$ $T_j = 150^{\circ}C$		1.6 1.5	2	V
t _{rr}	Reverse Recovery Time	$I_F = 50A$ $V_R = 300V$ di/dt =1800A/ μ s	$T_j = 25^{\circ}C$ $T_i = 150^{\circ}C$		100 150		ns
Q _{rr}	Reverse Recovery Charge		$T_j = 25^{\circ}C$ $T_i = 150^{\circ}C$		2.6 5.4		μC
Er	Reverse Recovery Energy		$T_j = 150 \text{ C}$ $T_j = 25^{\circ}\text{C}$ $T_i = 150^{\circ}\text{C}$		0.6 1.2		mJ
R _{thJC}	Junction to Case Thermal Resistance				1.2	1.42	°C/W

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Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

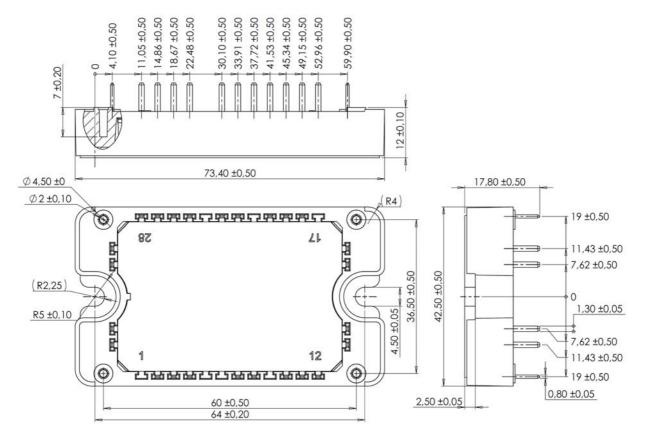
Symbol	Characteristic		Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
B _{25/85}	$T_{25} = 298.15 \text{ K}$			3952		Κ
$\Delta B/B$		$T_C=100^{\circ}C$		4		%
	2					

 $R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$ T: Thermistor temperature R_T: Thermistor value at T

Thermal and package characteristics

Symbol	Characteristic			Min	Max	Unit	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz					V	
TJ	Operating junction temperature range			-40	175	°C	
T _{JOP}	Recommended junction temperature under switching conditions			-40	T _J max -25		
T _{STG}	Storage Temperature Range			-40	125		
T _C	Operating Case Temperature			-40	125]	
Torque	Mounting torque	To heatsink	M4	2	3	N.m	
Wt	Package Weight				110	g	

Package outline (dimensions in mm)



See application note 1906 - Mounting Instructions for SP3F Power Modules on www.microsemi.com

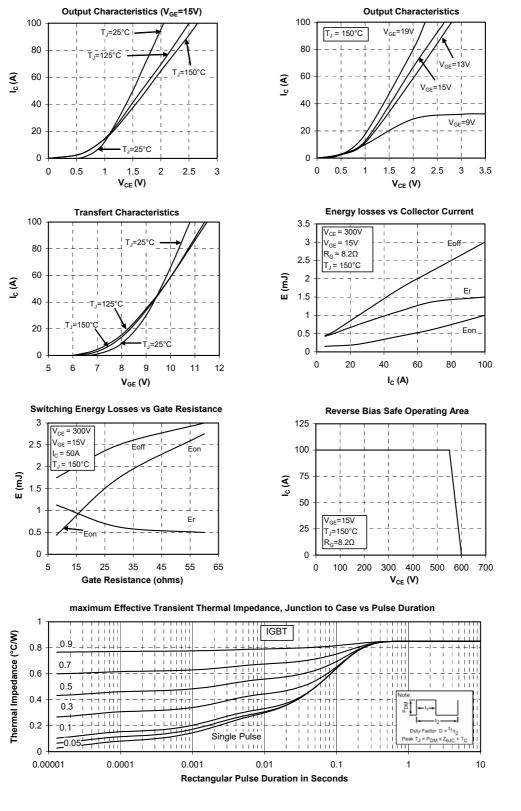
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Typical Performance Curve

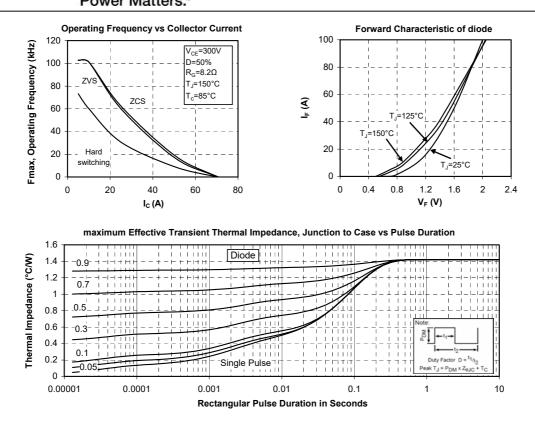


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